

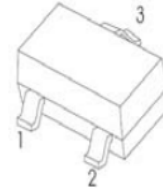
BC846,BC847,BC848

TRANSISTOR(NPN)

SOT-23

Features

1. Complementary to BC856,BC857,BC858
2. Power Dissipation of 200mW
3. High Stability and High Reliability



1: Base 2: Emitter 3: Collector

Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

参数 Parameters	符号 Symbol	TYPE	数值	单位 Unit
Collector-Base Voltage	V _{CBO}	BC846	80	V
		BC847	50	
		BC848	30	
Collector-Emitter Voltage	V _{CEO}	BC846	65	V
		BC847	45	
		BC848	30	
Emitter -Base Voltage	V _{EBO}		6	V
Collector Current-Continuous	I _C		100	mA
Collector Power Dissipation	P _C		200	mW
Junction Temperature	T _j		150	°C
Storage Temperature	T _{stg}		-40~150	°C

Electrical Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

Parameter	Symbols	Test Condition	Limits			Unit
			Min	Typ	Max	
Collector-base breakdown voltage	V(BR)CBO	I _C =10uA, I _E =0	BC846	80		V
			BC847	50		
			BC848	30		
Collector-emitter breakdown voltage	V(BR)CEO	I _C =10mA, I _B =0	BC846	65		V
			BC847	45		
			BC848	30		
Emitter-base breakdown voltage	V(BR)EBO	I _E =10uA, I _C =0	6			V
Collector cut-off current	I _{CBO}	V _{CB} =30V, I _E =0			100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0			100	nA
DC current gain	H _{fe}	V _{CE} =5V, I _C =2mA	110	800		
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =10mA, I _B =0.5mA			0.25	V
		I _C =100mA, I _B =5mA			0.5	
Base -emitter saturation voltage	V _{BE(sat)}	I _C =10mA, I _B =0.5mA			1	V
		I _C =100mA, I _B =5mA			1.2	
Transition frequency	f _T	V _{CE} =5V, I _C =10mA, f=100MHz		300		MHz

CLASSIFICATION OF hFE

RANK	A	B	C
RANGE	110-220	200-450	420-800

Typical Characteristics

